

WILK ELEKTRONIK S.A.

ul. Mikołowska 42, 43-173 Łaziska Górne, Poland

Website: www.goodram.com | www.wilk.com.pl

Tel: +48 (32) 736 90 00 Fax: +48 (32) 736 90 01

Wilk Elektronik S.A.

GOODRAM Industrial SD 3.0 (SLC, MLC, pSLC) Version 1.0

All rights are strictly reserved. Any portion of this paper shall not be reproduced, copied, or translated to any other forms without permission from Wilk Elektronik S.A.

This document is subjected to change without any notice.

Please contact your Wilk Elektronik S.A. sales representative for details as to environmental matters such as the RoHS compatibility of Product. Please use Product in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive. Wilk Elektronik S.A. assumes no liability for damages or losses occurring as a result of noncompliance with applicable laws and regulations.

Contents

1.	Intro	ductionduction	. 5
	1.1.	General Description	. 5
	1.2.	Flash Management	. 5
	•	Error Correction Code (ECC)	. 5
	•	Wear Leveling	. 5
	•	Bad Block Management	. 6
	•	Smart Function	. 6
	•	Auto-Read Refresh	. 6
	•	Pseudo SLC (pSLC)	. 7
2.	Prod	uct Specifications	. 8
3.	Envir	ronmental Specifications	11
	3.1.	Environmental Conditions	11
	0	Storage Temperature Range	11
	0	-40°C ~ 85°C	. 1
	0	Gold grade: -25°C ~ 85°C	11
	0	Diamond grade: -40°C ~ 85°C	11
4.	SD Ca	ard Comparison	15
5.	Elect	rical Specifications	16
	5.1.	Power Consumption	16
	5.2.	DC Characteristic	16
	•	Bus Operation Conditions for 3.3V Signaling	16
	•	Bus Signal Line Load	17

	•	Bus Operation Conditions – Signal Line's Load	. 18
	•	Power Up Time	. 18
	•	Power On or Power Cycle	. 18
	•	Power Supply Ramp Up	. 19
	•	Power Down and Power Cycle	. 19
	5.3.	AC Characteristic	. 19
	•	SD Interface Timing (Default)	. 20
	•	SD Interface Timing (High-Speed Mode)	. 21
	•	SD Interface Timing (SDR12, SDR25 and SDR50 Modes)	. 22
6.	Inter	face	26
	6.1.	Pad Assignment and Descriptions	. 26
7	Dhysi	ical Dimension	28

1. Introduction

1.1. General Description

The Secure Digital (SD) card version 3.0 is fully compliant with the specification released by SD Card

Association. The Command List supports [Part 1 Physical Layer Specification Ver3.01 Final] definitions. Card

capacities of non-secure area and secure area support [Part 3 Security Specification Ver3.0 Final]

Specifications.

The SD 3.0 card is based on 9-pin interface, designed to operate at a maximum operating frequency of

100MHz. It can alternate communication protocol between the SD mode and SPI mode. It performs data

error detection and correction with very low power consumption. The Card capacity could be more than

64GB and up to 2TB in the future with ex-FAT which is called SDXC (Extended Capacity SD Memory Card).

Secure Digital 3.0 card is one of the most popular cards today based on its high performance, good

reliability and wide compatibility.

1.2. Flash Management

Error Correction Code (ECC)

Flash memory cells will deteriorate with use, which might generate random bit errors in the stored data.

Thus, PS8032 applies the BCH ECC Algorithm, which can detect and correct errors occur during Read

process, ensure data been read correctly, as well as protect data from corruption.

Wear Leveling

GOODRAM logo is registered trademark of Wilk Elektronik S.A.

All products and specifications are subject to change without notice.

All other trademarks and logos are the property of their respective owners.

NAND Flash devices can only undergo a limited number of program/erase cycles, and in most cases, the

flash media are not used evenly. If some area get updated more frequently than others, the lifetime of the

device would be reduced significantly. Thus, Wear Leveling technique is applied to extend the lifespan of

NAND Flash by evenly distributing write and erase cycles across the media.

It provides advanced Wear Leveling algorithm, which can efficiently spread out the flash usage through the

whole flash media area. Moreover, by implementing both dynamic and static Wear Leveling algorithms, the

life expectancy of the NAND Flash is greatly improved.

Wilk Elektronik S.A. Poland, 43-173 Łaziska Górne, ul. Mikołowska 42 tel.: 0-32/ 736 90 00, fax: 0-32/ 736 90 01 www.wilk.com.pl I www.goodram.com

www.goodram.com

Bad Block Management

Bad blocks are blocks that include one or more invalid bits, and their reliability is not guaranteed. Blocks

that are identified and marked as bad by the manufacturer are referred to as "Initial Bad Blocks". Bad

blocks that are developed during the lifespan of the flash are named "Later Bad Blocks". It implements an

efficient bad block management algorithm to detect the factory-produced bad blocks and manages any bad

blocks that appear with use. This practice further prevents data being stored into bad blocks and improves

the data reliability.

Smart Function

SMART, an acronym for Self-Monitoring, Analysis and Reporting Technology, is an special function that

allows a memory device to automatically monitor its health. It provides a program named SmartInfo Tool to

observe 's SD cards. Note that this tool can only support 's PS8032 controller and industrial SD cards. This

tool will display the controller version, flash type, firmware version, endurance life ratio, good block ratio,

and so forth. In addition, a warning message will appear under the following 3 conditions:

(1) When the life ratio remained is less than 10%,

(2) When the amount of abnormal power on is more than **3,500** cycles, and

(3) When there are less than 5 usable blocks for replacing bad blocks.

Auto-Read Refresh

Auto-Read Refresh is especially applied on devices that read data mostly but rarely write data, such as GPS.

When blocks are continuously read, then the device cannot activate wear leveling since it can only be

applied while writing data. Thus, errors will accumulate and become uncorrectable. Accordingly, to avoid

errors exceed the amount ECC can correct and blocks turn bad, 's firmware will automatically refresh the

bit errors when the error number in one block approaches the threshold, ex., 24 bits.

• Pseudo SLC (pSLC)

Pseudo SLC can be considered as an extended version of MLC. While MLC contains fast and slow pages, pSLC only applies fast pages for programming. The concept of pSLC is demonstrated in the two tables below. The first and second bits of a memory cell represent a fast and slow page respectively, as shown in the left table. Since only fast pages are programmed when applying pSLC, the bits highlighted in red are used, as shown in the right table. Accordingly, because only fast pages are programmed, pSLC provides better performance and endurance than MLC. Moreover, pSLC performs similarly with SLC, yet pSLC is more cost-effective.

MLC Flash		
1st Bit (Fast page)	2nd Bit (Slow page)	
1	1	
1	0	
0	1	
0	0	

Pseudo S	SLC Flash
1st Bit (Fast page)	2nd Bit (Slow page)
1	1
1	0
0	1
0	0

Cell Content of MLC (Left) and pSLC (Right)

2. Product Specifications

- Capacity
 - SLC: 4GB up to 32GB (Diamond & Gold)
 - MLC: 4GB up to 64GB (Diamond & Gold)
 - o pSLC: 2GB up to 32GB (Diamond & Gold)
- Operation Temp. Range
 - Gold Series: -25~85°C (SLC & MLC)
 - Diamond Series: -40~+85°C (SLC & MLC)
- Storage Temp. Range
 - o -40~+85°C
- Support SD system specification version 3.0
- Card capacity of non-secure area and secure area support [Part 3 Security Specification Ver3.0
 Final] Specifications
- Support SD SPI mode
- Designed for read-only and read/write cards
- Bus Speed Mode (use 4 parallel data lines)
 - Non-UHS mode
 - Default speed mode: 3.3V signaling, frequency up to 25MHz, up to 12.5 MB/sec
 - High speed mode: 3.3V signaling, frequency up to 50MHz, up to 25 MB/sec

Note: SDSC card (capacity less than and including 2GB) only supports non-UHS mode.

- UHS-I mode
 - SDR12: SDR up to 25MHz, 1.8V signaling
 - SDR25: SDR up to 50MHz, 1.8V signaling
 - SDR50: 1.8V signaling, frequency up to 100MHz, up to 50 MB/sec
 - DDR50: 1.8V signaling, frequency up to 50MHz, sampled on both clock edges, up to 50
 MB/sec

Note: Timing in 1.8V signaling is different from that of 3.3V signaling.

• The command list supports [Part 1 Physical Layer Specification Ver3.1 Final] definitions

- Copyrights Protection Mechanism
 - Compliant with the highest security of SDMI standard
- Support CPRM (Content Protection for Recordable Media) of SD Card
- Card removal during read operation will never harm the content
- Password Protection of cards (optional)
- Write Protect feature using mechanical switch
- Built-in write protection features (permanent and temporary)
- +4KV/-4KV ESD protection in contact pads
- Operation voltage range: 2.7 ~ 3.6V
- Performance

o SLC

Conscitu	Mode	Flash Structure	Sequ	ential
Capacity	iviode	riash Structure	Read (MB/s)	Write (MB/s)
4GB	UHS-I	TSB 24nm 4GB x 1	27	23
8GB	UHS-I	TSB 24nm 8GB x 1	27	25
16GB	UHS-I	TSB 24nm 16GB x 1	27	25
32GB	UHS-I	TSB 24nm 16GB x 2	27	25

o MLC

Canacitu	Mode	Flash Structure	Seque	ential
Capacity	iviode	riash Structure	Read (MB/s)	Write (MB/s)
4GB	UHS-I	TSB 19nm 4GB x 1	26	10
8GB	UHS-I	TSB 19nm 8GB x 1	26	10
16GB	UHS-I	TSB 19nm 16GB x 1	26	10
32GB	UHS-I	TSB 19nm 32GB x 1	26	10
64GB	UHS-I	TSB 19nm 32GB x 2	26	15

o pSLC

Conneity	Mode	Floob Stanieture	Seque	ential
Capacity	Mode	Flash Structure	Read (MB/s)	Write (MB/s)

2GB	Non-UHS	TSB 19nm 4GB x 1	20	20
4GB	UHS-I	TSB 19nm 8GB x 1	26	24
8GB	UHS-I	TSB 19nm 16GB x 1	26	24
16GB	UHS-I	TSB 19nm 32GB x 1	26	24
32GB	UHS-I	TSB 19nm 32GB x 2	26	24

NOTES:

- 1. The performance is obtained from TestMetrix Test.
- 2. Samples are made of Toshiba 24nm SLC and 19nm MLC Toggle NAND Flash.
- 3. Performance may vary from flash configuration and platform.
- 4. The table above is for your reference only. The criteria for MP (mass production) and for accepting goods shall be discussed based on different flash configuration.

3. Environmental Specifications

3.1. Environmental Conditions

- Temperature and Humidity
 - Storage Temperature Range
 - o -40°C ~ 85°C
- Operation Temperature Range

Gold grade: -25°C ~ 85°C

Diamond grade: -40°C ~ 85°C

High Temperature Test Condition (Gold Series)

	Temperature	Humidity	Test Time
Operation	85°C	0% RH	168 hours
Storage	85°C	0% RH	500 hours

Result: No any abnormality is detected.

High Temperature Test Condition (Diamond Series)

	Temperature	Humidity	Test Time
Operation	85°C	0% RH	300 hours
Storage	85°C	0% RH	500 hours

Result: No any abnormality is detected.

Low Temperature Test Condition (Gold Series)

	Temperature	Humidity	Test Time
Operation	-25°C	0% RH	168 hours
Storage	-40°C	0% RH	300 hours

Result: No any abnormality is detected.

Low Temperature Test Condition (Diamond Series)

Temperature	Humidity	Test Time
-------------	----------	-----------

Operation	-40°C	0% RH	168 hours
Storage	-40°C	0% RH	500 hours

Result: No any abnormality is detected.

High Humidity Test Condition (Gold Series)

	Temperature	Humidity	Test Time
Operation	40°C	95% RH	4 hours
Storage	40°C	95% RH	500 hours

Result: No any abnormality is detected.

High Humidity Test Condition (Diamond Series)

	Temperature	Humidity	Test Time
Operation	55°C	95% RH	4 hours
Storage	55°C	95% RH	500 hours

Result: No any abnormality is detected.

Temperature Cycle Test (Gold Series)

	Temperature	Test Time	Cycle	
Operation	-25°C	30 min	20 Oveles	
Operation	85°C	30 min	20 Cycles	
Storago	-40°C	30 min	20 Ovelos	
Storage	85°C	30 min	20 Cycles	

Result: No any abnormality is detected.

Temperature Cycle Test (Diamond Series)

	Temperature	Test Time	Cycle	
Operation	-40°C	30 min	20 Oveles	
Operation	85°C	30 min	20 Cycles	
Storege	-40°C	30 min	FO Cycles	
Storage	85°C	30 min	50 Cycles	

Result: No any abnormality is detected.

Shock

Shock Specification

	Acceleration Force	Half Sin Pulse Duration
Industrial SD card	1500G	0.5ms

Result: No any abnormality is detected when power on.

Vibration

Vibration Specification

	Condition		Vibration Orientation
	Frequency/Displacement	Frequency/Acceleration	Vibration Orientation
Industrial SD card	20Hz~80Hz/1.52mm	80Hz~2000Hz/20G	X, Y, Z axis/30 min for
			each

Result: No any abnormality is detected when power on.

Drop

Drop Specification

	Height of Drop	Number of Drop
Industrial SD card	150cm free fall	6 face of each unit

Result: No any abnormality is detected when power on.

Bending

Bending Specification

	Force	Action
Industrial SD card	≥ 10N	Hold 1min/5times

Result: No any abnormality is detected when power on.

• Torque

Torque Specification

Force Action

es

Result: No any abnormality is detected when power on.

• Electrostatic Discharge (ESD)

Contact ESD Specification

	Condition	Result
Industrial SD card	Contact: +/- 4KV each item 25 times Air: +/- 8KV 10 times	PASS

• EMI Compliance

o FCC: CISPR22

O CE: EN55022

o **BSMI 13438**

4. SD Card Comparison

Comparing SD3.0 Standard and SD3.0 SDXC

	SD3.0 Standard (Backward compatible to 2.0 host)	SD3.0 SDHC (Backward compatible to 2.0 host)	SD3.0 SDXC	
Addressing Mode	Byte (1 byte unit)	Block (512 byte unit)	Block (512 byte unit)	
HCS/CCS bits of ACMD41	Support	Support	Support	
CMD8 (SEND_IF_COND)	Support	Support	Support	
CMD16 (SET_BLOCKLEN)	Support	Support (Only CMD42)	Support (Only CMD42)	
Partial Read	Support	Not Support	Not Support	
Lock/Unlock Function	Mandatory	Mandatory	Mandatory	
Write Protect Groups	Optional	Not Support	Not Support	
Supply Voltage 2.0v – 2.7v (for initialization)	Not Support	Not Support	Not Support	
Total Bus Capacitance for each signal line	40pF	40pF	40pF	
CSD Version (CSD_STRUCTURE Value)	1.0 (0x0)	2.0 (0x1)	2.0 (0x1)	
Speed Class	Optional	Mandatory (Class 2 / 4 / 6 / 10)	Mandatory (Class 2 / 4 / 6 / 10)	

5. Electrical Specifications

5.1. Power Consumption

The table below is the power consumption of PS8032 with different flash memory types.

Power Consumption of PS8032 Industrial SD card

Flash Mode	Max. Power Up	Max. Standby	Max. Read Current (mA)	Max. Write Current (mA)	
Single Flash ^{Note1}	Current (uA)	Current (uA) 150	100	100	
(1 x 8bit) SDR/DDR	250	250	200	200	

NOTE:

1. Data transfer mode is single channel.

5.2. DC Characteristic

• Bus Operation Conditions for 3.3V Signaling

Threshold Level for High Voltage Range

Parameter	Symbol	Min.	Max	Unit	Condition
Supply Voltage	VDD	2.7	3.6	٧	
Output High Voltage	VOH	0.75*VDD		٧	IOH=-2mA VDD Min
Output Low Voltage	VOL		0.125*VDD	>	IOL=2mA VDD Min
Input High Voltage	VIH	0.625*VDD	VDD+0.3	٧	
Input Low Voltage	VIL	VSS-0.3	0.25*VDD	V	
Power Up Time			250	ms	From 0V to VDD min

Peak Voltage and Leakage Current

Parameter	Symbol	Min	Max.	Unit	Remarks	
Peak voltage on all lines		-0.3	V _{DD} +0.3	V		
All Inputs						
Input Leakage Current		-10	10	uA		
All Outputs						
Output Leakage Current		-10	10	uA		

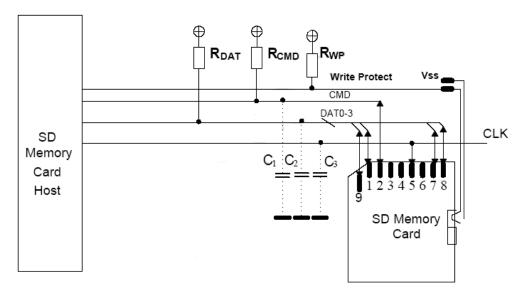
Threshold Level for 1.8V Signaling

Parameter	Symbol	Min.	Max	Unit	Condition
Supply Voltage	VDD	2.7	3.6	V	
Regulator Voltage	VDDIO	1.7	1.95	V	Generated by VDD
Output High Voltage	VOH	1.4	-	V	IOH=-2mA
Output Low Voltage	VOL	-	0.45	V	IOL=2mA
Input High Voltage	VIH	1.27	2.00	V	
Input Low Voltage	VIL	Vss-0.3	0.58	V	

Input Leakage Current for 1.8V Signaling

Parameter	Symbol	Min	Max.	Unit	Remarks
Input Lookage Current		1	2		DAT3 pull-up is
Input Leakage Current		-2	2	uA	disconnected.

• Bus Signal Line Load



Bus Circuitry Diagram

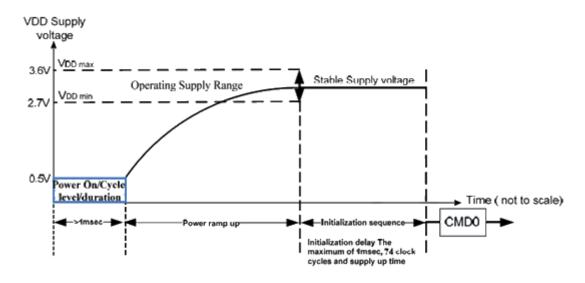
Bus Operation Conditions – Signal Line's Load

Total Bus Capacitance = CHOST + CBUS + N CCARD

Parameter	symbol	Min	Max	Unit	Remark
Pull-up resistance	R _{CMD}	10	100	kΩ	to prevent bus floating
Total bus capacitance for each signal line	C _L		40	pF	1 card CHOST+CBUS shall not exceed 30 pF
Card Capacitance for each signal pin	CCARD		10	pF	
Maximum signal line inductance			16	nH	
Pull-up resistance inside card (pin1)	RDAT3	10	90	kΩ	May be used for card detection
Capacity Connected to Power Line	СС		5	uF	To prevent inrush current

Power Up Time

Host needs to keep power line level less than 0.5V and more than 1ms before power ramp up.



• Power On or Power Cycle

Followings are requirements for Power on and Power cycle to assure a reliable SD Card hard reset.

- (1) Voltage level shall be below 0.5V.
- (2) Duration shall be at least 1ms.

Power Supply Ramp Up

The power ramp up time is defined from 0.5V threshold level up to the operating supply voltage which is stable between VDD (min.) and VDD (max.) and host can supply SDCLK.

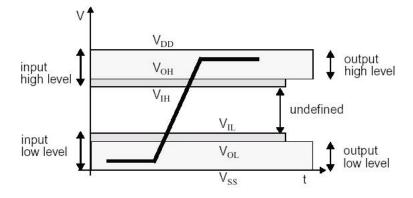
Followings are recommendations of Power ramp up:

- (1) Voltage of power ramp up should be monotonic as much as possible.
- (2) The minimum ramp up time should be 0.1ms.
- (3) The maximum ramp up time should be 35ms for 2.7-3.6V power supply.

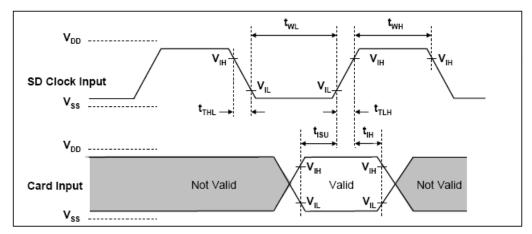
• Power Down and Power Cycle

- (1) When the host shuts down the power, the card VDD shall be lowered to less than 0.5Volt for a minimum period of 1ms. During power down, DAT, CMD, and CLK should be disconnected or driven to logical 0 by the host to avoid a situation that the operating current is drawn through the signal lines.
- (2) If the host needs to change the operating voltage, a power cycle is required. Power cycle means the power is turned off and supplied again. Power cycle is also needed for accessing cards that are already in *Inactive State*. To create a power cycle the host shall follow the power down description before power up the card (i.e. the card VDD shall be once lowered to less than 0.5Volt for a minimum period of 1ms).

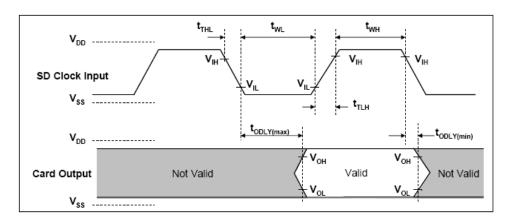
5.3. AC Characteristic



• SD Interface Timing (Default)



Card Input Timing (Default Speed Card)



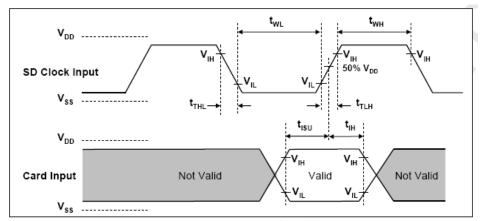
Card Output Timing (Default Speed Mode)

Parameter	Symbol	Min	Max	Unit	Remark		
Clock CLK (All v	alues are re	ferred to m	in(V _H) and max	(V _{IL})			
Clock frequency Data Transfer Mode	f_{pp}	0	25	MHz	C _{card} ≤?10 pF (1 card)		
Clock frequency Identification Mode	f _{od}	0(1)/100	400	kHz	C _{card} ≤?10 pF (1 card)		
Clock low time	t _{wL}	10		ns	C _{card} ≤?10 pF (1 card)		
Clock high time	t _{wн}	10		ns	C _{card} ≤?10 pF (1 card)		
Clock rise time	t _{TLH}		10	ns	C _{card} ≤?10 pF (1 card)		
Clock fall time	t _{THL}		10	ns	C _{card} ≤॒?10 pF (1 card)		
Inputs CMD, DAT (referenced to CLK)							
Input set-up time	t _{ISU}	5		ns	C _{card} ≤⊡10 pF (1 card)		

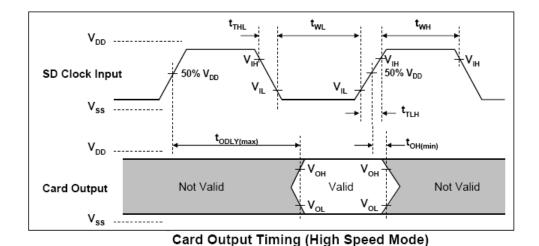
Input hold time	t _{IH}	5		ns	C _{card} ≤॒?10 pF (1 card)			
Outputs CMD, DAT (referenced to CLK)								
Output Delay time during Data Transfer Mode	t _{ODLY}	0	14	ns	C _L ≤40 pF (1 card)			
Output Delay time during	tODLY	0	50	ns	C ₁ ≤40 pF			
Identification Mode	TODLY	U	30	115	(1 card)			

^{(1) 0}Hz means to stop the clock. The given minimum frequency range is for cases where continuous clock is required.

• SD Interface Timing (High-Speed Mode)



Card Input Timing (High Speed Card)



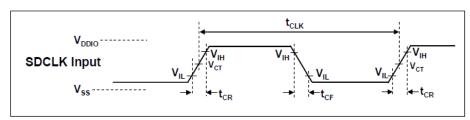
Symbol **Parameter** Min Max Unit Remark Clock CLK (All values are referred to $min(V_{IH})$ and $max(V_{IL})$ Clock frequency Data Transfer $C_{card} \le 10 pF$ f_{PP} 0 50 MHz Mode (1 card) Clock low time $C_{card} \le 10 pF$ t_{WL}

					(1 card)		
Clock high time	t _{wh}	7		ns	C _{card} ≤ 10 pF (1 card)		
Clock rise time	t _{TLH}		3	ns	C _{card} ≤ 10 pF (1 card)		
Clock fall time	t _{THL}		3	ns	C _{card} ≤ 10 pF (1 card)		
Inputs CMD, DAT (referenced to CLK)							
Input set-up time	t _{ISU}	6		ns	C _{card} ≤ 10 pF (1 card)		
Input hold time	t _{iH}	2		ns	C _{card} ≤ 10 pF (1 card)		
Outpu	ts CMD, DA	T (referenc	ed to CLK)				
Output Delay time during Data Transfer Mode	t _{odly}		14	ns	C _L ≤ 40 pF (1 card)		
Output Hold time	Тон	2.5		ns	C _L ≤ 15 pF (1 card)		
Total System capacitance of each line ¹	C _L		40	pF	CL ≤ 15 pF (1 card)		

⁽¹⁾ In order to satisfy severe timing, the host shall drive only one card.

• SD Interface Timing (SDR12, SDR25 and SDR50 Modes)

Input

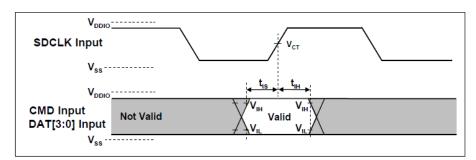


Clock Signal Timing

Clock Signal Timing

Symbol	Min	Max	Unit	Remark
tCLK	4.80	1	ns	208MHz (Max.), Between rising edge, VCT= 0.975V
tCR, tCF	-	0.2* tCLK	ns	tCR, tCF < 2.00ns (max.) at 100MHz, CCARD=10pF
Clock Duty	30	70	%	

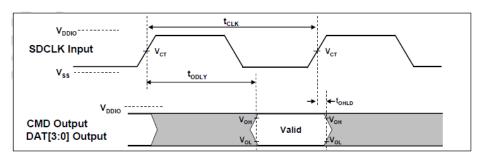
SDR50 Input Timing



Card Input Timing

Ī	Symbol	Min	Max	Unit	SDR50 Mode
ĺ	tls	3.00	-	ns	CCARD =10pF, VCT= 0.975V
ĺ	tIH	0.80	-	ns	CCARD =5pF, VCT= 0.975V

Output

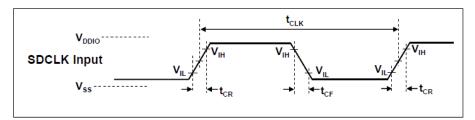


Output Timing of Fixed Data Window

Output Timing of Fixed Data Window

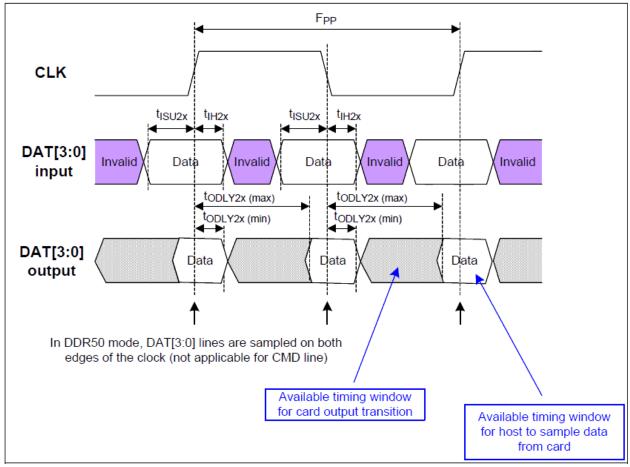
Symbol	Min	Max	Unit	Remark
tODLY	-	7.5	ns	tCLK>=10.0ns, CL=30pF, using driver Type B, for SDR50
tODLY	-	14	ns	tCLK>=20.0ns, CL=40pF, using driver Type B, for SDR25 and SDR12,
ТОН	1.5	-	ns	Hold time at the tODLY (min.), CL=15pF

SD Interface Timing (DDR50 Mode)



Clock Signal Timing

Symbol	Min	Max	Unit	Jnit Remark	
tCLK	20	-	ns	50MHz (Max.), Between rising edge	
tCR, tCF	-	0.2* tCLK	ns	tCR, tCF < 4.00ns (max.) at 50MHz, CCARD=10pF	
Clock Duty	45	55	%		



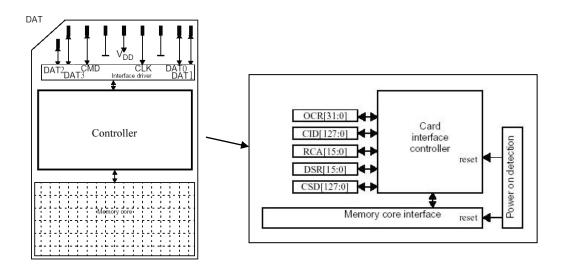
Timing Diagram DAT Inputs/Outputs Referenced to CLK in DDR50 Mode

Bus Timings – Parameters Values (DDR50 Mode)

Parameter	Symbol	Min	Max	Unit	Remark		
		l		Unit	Keiliaik		
Input CMD (referenced to CLK rising edge)							
Input set-up time	t _{ISU}	6	_	ns	C _{card} ≤፻10 pF		
input set up time	LISU				(1 card)		
Lancit hadding	t _{IH}	0.0		ns	C _{card} ≤፻10 pF		
Input hold time		0.8	-		(1 card)		
Output (Output CMD (referenced to CLK rising edge)						
Output Delay time during Data	t _{ODLY}		13.7	ns	C _L ≤30 pF		
Transfer Mode					(1 card)		
0.1	Тон	1.5		ns	C _L ≥15 pF		
Output Hold time			-		(1 card)		
Inputs DAT (referenced to CLK rising and falling edges)							
	t _{ISU2x}	3		ns	C _{card} ≤፻10 pF		
Input set-up time			-		(1 card)		
Lead to the latter of		0.0		ns	C _{card} ≤፻10 pF		
Input hold time	t _{IH2x}	0.8	-		(1 card)		
Outputs DAT (referenced to CLK rising and falling edges)							
Output Delay time during Data	_	-	7.0	ns	C _L ≤25 pF		
Transfer Mode	t _{ODLY2x}				(1 card)		
Outout Hold time	T _{OH2x}	1.5	-	ns	C _L ≥15 pF		
Output Hold time					(1 card)		

6. Interface

6.1. Pad Assignment and Descriptions



SD Memory Card Pad Assignment

pin		SD	Mode	SPI Mode			
	Name	Type ¹	Description	Name	Туре	Description	
1	CD/DAT3 ²	I/O/PP ³	Card Detect/ Data Line[bit3]	CS	I 3	Chip Select (net true)	
2	CMD	PP	Command/Response	DI	I	Data In	
3	V_{SS1}	S	Supply voltage ground	VSS	S	Supply voltage ground	
4	V_{DD}	S	Supply voltage	VDD	S	Supply voltage	
5	CLK	I	Clock	SCLK	I	Clock	
6	V_{SS2}	S	Supply voltage ground	VSS2	S	Supply voltage ground	
7	DAT0	I/O/PP	Data Line[bit0]	DO	O/PP	Data Out	
8	DAT1	I/O/PP	Data Line[bit1]	RSV			
9	DAT2	I/O/PP	Data Line[bit2]	RSV			

- (1) S: power supply, I: input; O: output using push-pull drivers; PP: I/O using push-pull drivers.
- (2) The extended DAT lines (DAT1-DAT3) are input on power up. They start to operate as DAT lines after SET_BUS_WIDTH command. The Host shall keep its own DAT1-DAT3 lines in input mode as well while they are not used. It is defined so in order to keep compatibility to MultiMedia Cards.
- (3) At power up, this line has a 50KOhm pull up enabled in the card. This resistor serves two functions: Card detection and Mode Selection. For Mode Selection, the host can drive the line high or let it be

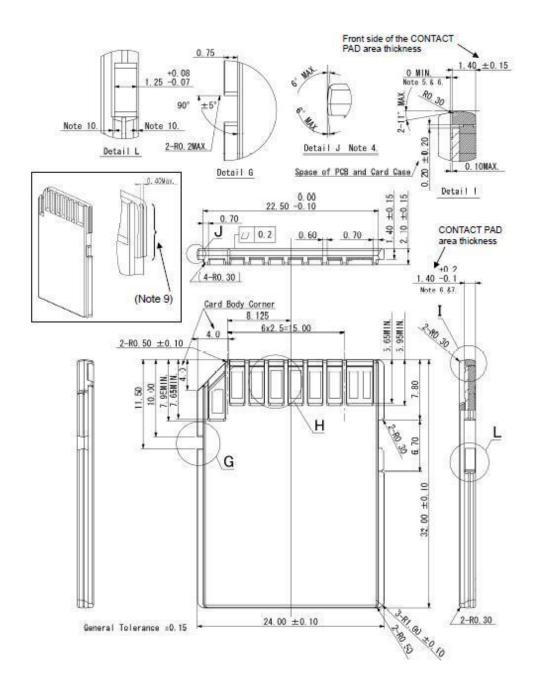
pulled high to select SD mode. If the host wants to select SPI mode, it should drive the line low. For Card detection, the host detects that the line is pulled high. This pull-up should be disconnected by the user during regular data transfer with SET_CLR_CARD_DETECT (ACMD42) command.

Name	Width	Description
CID	4.20k:t	Card identification number; card individual number for identification.
CID 128bit		Mandatory
		Relative card address; local system address of a card, dynamically
RCA1	16bit	suggested by the card and approved by the host during initialization.
		Mandatory
DSR	16bit	Driver Stage Register; to configure the card's output drivers. Optional
CSD	128bit	Card Specific Data; information about the card operation conditions.
		Mandatory
CCD	641.11	SD Configuration Register; information about the SD Memory Card's Special
SCR 64bit	04DIL	Features capabilities Mandatory
OCR	32bit	Operation conditions register. Mandatory.
SSR	512bit	SD Status; information about the card proprietary features
		Mandatory
OCR	32bit	Card Status; information about the card status
UCK		Mandatory

⁽¹⁾ RCA register is not used (or available) in SPI mode.

7. Physical Dimension

Dimension: 32mm(L) x 24mm(W) x 2.1mm(H)



Warning

- Do not bend, crush, drop, or place heavy objects on top of the Product. Do not use tweezers, pliers, or similar items that could damage the Product. Take particular care when inserting or removing the Product. Stop using the Product when the Product does not work properly. Failure to follow these instructions could result in fire, damage to the Product and/or other property, and/or personal injury including burns and electric shock.
- Keep out of reach of small children. Accidental swallowing may cause suffocation or injury. Contact a doctor immediately if you suspect a child has swallowed the Product. .
- Do not directly touch the interface pins, put them in contact with metal, strike them with hard objects, or cause them to short. Do not expose to static electricity.
- Do not disassemble or modify the Product. This may cause electric shock, damage to the Product, or fire.

Notes on usage

- The Product contains nonvolatile semiconductor memory. Do not use the Product in accordance with a method of usage other than that written in the manual. This may cause the destruction or loss of data.
- To protect against accidental data loss, you should back up your data frequently on more than one type of storage media. **** Corporation assumes no liability for destruction or loss of data recorded on the Card for any reason.
- When used over a long period of time or repeatedly, the reading, writing and deleting capabilities of the Product will eventually fail, and the performance speed of the Product may decrease below the original speed specific to the Product's applicable class.
- If the Product is to be transferred or destroyed, note that the data it contained may still be recoverable unless it is permanently deleted by third-party deletion software or similar means beforehand.

Product applications and design.

Product is intended for use in general electronics applications (e.g., computers, personal equipment, office equipment, measuring equipment, industrial robots and home electronics appliances) or for specific applications as expressly stated in this document. Product is neither intended nor warranted for use in equipment or systems that require extraordinarily high levels of quality and/or reliability and/or a malfunction or failure of which may cause loss of human life, bodily injury, serious property damage or serious public impact ("Unintended Use"). Unintended Use includes, without limitation, equipment used in nuclear facilities, equipment used in the aerospace industry, medical equipment, equipment used for automobiles, trains, ships and other transportation, traffic signaling equipment, equipment used to control combustions or explosions, safety devices, elevators and escalators, devices related to electric power, and equipment used in finance-related fields. Do not use Product for Unintended Use unless specifically permitted in this document.

No parts of this document may be reproduced, stored in a retrieval system, or transmitted, in any form or by any means, mechanical ,electric, photocopying, recording or otherwise, without permission of Wilk Elektronik S.A. Wilk Elektronik S.A does not make any warranty ,express or implied, with respect to this document, including as to licensing, Non-infringement, merchantability or fitness for a particular purpose.